11th RD50 Workshop

Monday 12 November 2007

Pad Detector Characterization & Defect Engineering - 40-S2-C01 (15:50 - 18:00)

time	[id] title	presenter
	[29] TCT and CCE measurements for 9 MeV and 24 GeV/c irradiated n-type MCz-Si pad detectors	Dr HAERKOENEN, Jaakko
16:10	[15] First results on 24 GeV/c proton irradiated thin silicon detectors	FRETWURST, Eckhart
16:30	[3] Epitaxial silicon detectors irradiated with protons and neutrons	KASKA, Katharina
	[8] Determination of Trapping Time Constants in Neutron Irradiated Thin Epitaxial Pad Detectors	WEBER, Jens
17:10	[34] First results on electric field distribution in irradiated epi-Si detectors	Dr VERBITSKAYA, Elena
17:30	[19] Discussion session	